

Description

The BSS7728N uses advanced trench technology

to provide excellent $R_{\text{DS}(\text{ON})},$ low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

General Features

V_{DS} = 60V I_D =0.3A

 $R_{DS(ON)} < 2\Omega @ V_{GS}=10V$

ESD Rating: HBM≥2000V

Application

Battery protection

Load switch

Uninterruptible power supply

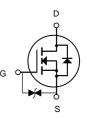
Package Marking and Ordering Information

 <u> </u>	U		
Product ID	Pack	Brand	Qty(PCS)
BSS7728N	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (Tc=25°Cunless otherwise noted)

Symbol	Parameter		Limit	Unit
Vds	Drain-Source Voltage		60	V
Vgs	Gate-Source Voltage	Gate-Source Voltage		V
	Continuous Drain Current (TJ =150℃)	T _A =25℃	0.3	
l _D		T _A =100 °C	0.19	A
Ідм	Drain Current-Pulsed (Note 1)	rain Current-Pulsed (Note 1)		А
PD	Maximum Power Dissipation		0.35	W
Тј,Тѕтб	Operating Junction and Storage Temperature Range		-55 To 150	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)		350	°C /W





N-Channel MOSFET



Electrical Characteristics (T_A=25 $^{\circ}$ Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	60	68	-	V
Zero Gate Voltage Drain Current	ldss	V _{DS} =60V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	Igss	V _{GS} =±10V,V _{DS} =0V V _{GS} =±20V,V _{DS} =0V	-	±100 ±4	±500 ±10	nA uA
Gate Threshold Voltage	VGS(th)	V _{DS} =V _{GS} ,I _D =250µA	0.7	1.2	1.9	V
		V _{GS} =5V, I _D =0.1A	-	1.3	3	Ω
Drain-Source On-State Resistance	Rds(on)	V _{GS} =10V, I _D =0.1A	-	1	2	Ω
Forward Transconductance	gfs	V _{DS} =10V,I _D =0.2A	0.1	-	-	S
Input Capacitance	C _{ISS}		-	21	50	PF
Output Capacitance	Coss	V _{DS} =25V,V _{GS} =0V, F=1.0MHz	-	11	25	PF
Reverse Transfer Capacitance	Crss		-	4.2	5	PF
Turn-on Delay Time	td(on)		-	10	-	nS
Turn-on Rise Time	tr	VDD=30V,ID=0.2A	-	50	-	nS
Turn-Off Delay Time	td(off)	V_{GS} =10V,R _{GEN} =10Ω	-	17	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg	V _{DS} =10V,I _D =0.3A, V _{GS} =4.5V	-	1.7	3	nC
Diode Forward Voltage (Note 3)	Vsd	V _{GS} =0V,I _S =0.2A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	0.3	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production



Typical Electrical And Thermal Characteristics

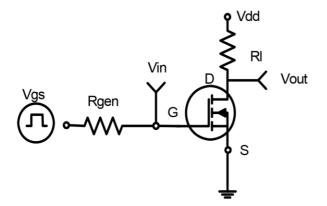


Figure 1:Switching Test Circuit

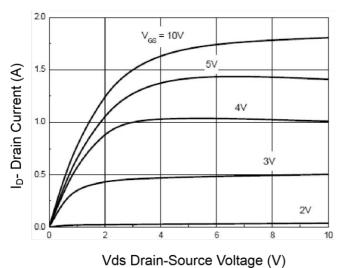
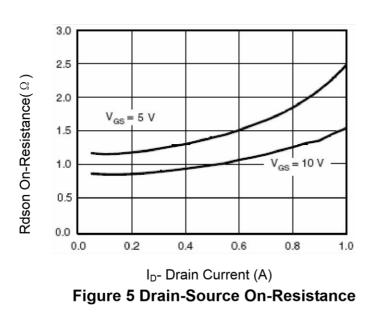


Figure 3 Output Characteristics



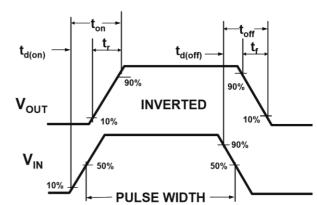


Figure 2:Switching Waveforms

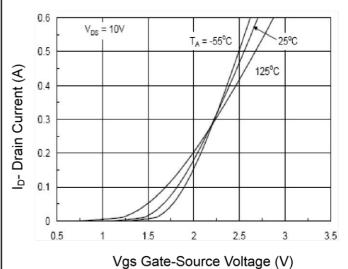
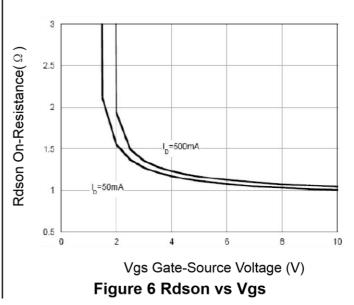
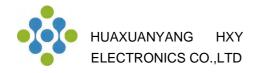
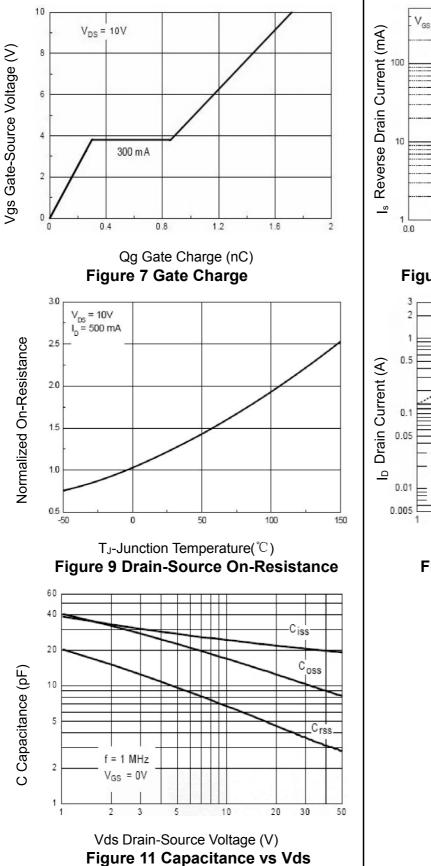
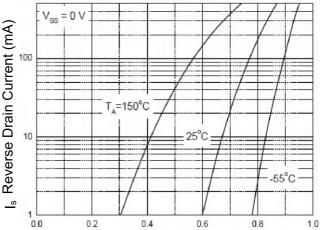


Figure 4 Transfer Characteristics

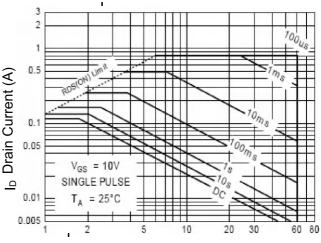








Vsd Source-Drain Voltage (V) Figure 8 Source-DrainDiode Forward



Vds Drain-Source Voltage (V) Figure 10 Safe Operation Area



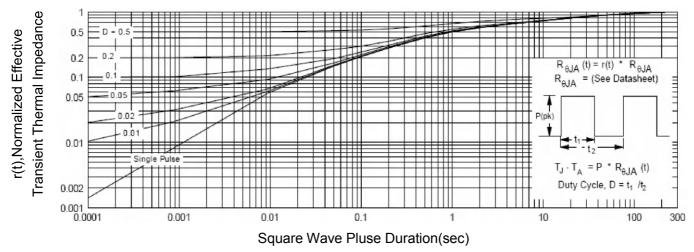
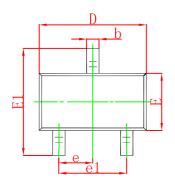
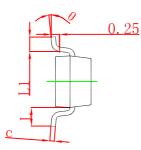


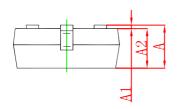
Figure 12 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Outline Dimensions

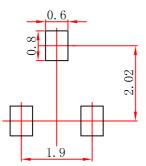






Sumphal	Dimensions In Millimeters		Dimensions In Inches			
Symbol	Min	Max	Min	Max		
Α	0.900	1.150	0.035	0.045		
A1	0.000	0.100	0.000	0.004		
A2	0.900	1.050	0.035	0.041		
b	0.300	0.500	0.012	0.020		
С	0.080	0.150	0.003	0.006		
D	2.800	3.000	0.110	0.118		
Е	1.200	1.400	0.047	0.055		
E1	2.250	2.550	0.089	0.100		
e	0.950	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079		
L	0.550 REF		0.022 REF			
L1	0.300	0.500	0.012	0.020		
θ	0°	8°	0°	8°		

SOT-23 Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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